

PTO/SB/08A (10-01)

Approved for use through 10/31/2002; OMB 0651-0031

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Substitute for form 1449A/PTO

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Sheet

1

of

3

Complete if Known

Application Number:

10602.436

Filing Date:

06-23-03

First Named Inventor

Jong-Jan Lee

Art Unit

281

Examiner Name.

44. VU

Attorney Docket Number

SLA0733

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code (if known)	MM-DD-YYYY		
✓		US- 6,413,802 B1	07-02-2002	Hu et al.	
		US- 6,432,829 B2	08-13-2002	Muller et al.	
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	US-				
	US-				
	US-				
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[illegible]

Examiner
Signature

HUNG VU

Date: _____

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02/07/06

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
Application Number:	w/603,436	Filing Date:	06-23-03
First Named Inventor:	Sheng Teng Hsu	Group/Art Unit:	2891
Examiner Name:	H. V.	Attorney Docket Number:	SLA0733
Sheet 2	of 3		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published	T ²
√		N. SUGIYAMA, T. MIZUNO, S. TAKAGI, M. KOIKE, A. KUROBE, <i>Formation of strained-silicon layer on thin relaxed SiGe/SiO₂/Si structure using SIMOX technology</i> , Thin Solid Films, 396 (2000) 199-202.	
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V		Y-K. CHOI, N. LINDERT, P. XUAN, S. TANG, D. HA, E. ANDERSON, T-J. KING, J. BOKOR, C. HU, <i>Sub-20 nm CMOS finFET technologies</i> , IEDM Tech. Dig., 2001.	

Examiner Signature:	HUNG VU	Date:	02/07/06
		Considered	

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First Named Inventor		Sheng Teng Hsu			
Group/Art Unit		2811			
Examiner Name		H. Ju			
Attorney Docket Number		SLA0733			
Sheet	3	of	3		

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Examiner Signature:	HUNG VU	Date Considered	02/07/06
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